

#### **Description**

The Si3932DV uses advanced trench technology to provide excellent R<sub>DS(ON)</sub>, low gate charge and operation with gate voltages as low as 2.5V. This device is suitable for use as a Battery protection or in other Switching application.



SOT-23-6L

#### **General Features**

V<sub>DS</sub> = 30V I<sub>D</sub> = 4.5 A

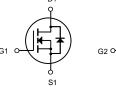
 $R_{DS(ON)} < 38m\Omega$  @  $V_{GS}=10 V$ 

### **Application**

Battery protection

Load switch

Uninterruptible power supply





**Dual N-Channel MOSFET** 

### **Package Marking and Ordering Information**

Product ID	Pack	Brand	Qty(PCS)
Si3932DV	SOT-23-6L	HXY MOSFET	3000

## Absolute Maximum Ratings@T<sub>j</sub>=25°C(unless otherwise specified)

Symbol	Parameter	Rating	Units
V <sub>DS</sub>	Drain-Source Voltage	30	V
V <sub>G</sub> S	Gate-Source Voltage	<u>+</u> 12	V
I <sub>D</sub> @T <sub>A</sub> =25°C	Drain Current, V <sub>GS</sub> @ 4.5V <sup>3</sup>	4.5	Α
Ірм	Pulsed Drain Current <sup>1</sup>	15	А
P <sub>D</sub> @T <sub>A</sub> =25°C	Total Power Dissipation	1.25	W
Тѕтс	Storage Temperature Range	-55 to 150	°C
TJ	Operating Junction Temperature Range	-55 to 150	°C
Rthj-a	Maximum Thermal Resistance, Junction- ambient <sup>3</sup>	125	°C/W



# **Electrical Characteristics** (T<sub>J</sub>=25 °C unless otherwise specified)

Symbol	Parameter	Test Condition	Min.	Тур.	Max.	Units
V <sub>(BR)DSS</sub>	Drain-Source Breakdown Voltage	V <sub>GS</sub> =0V, I <sub>D</sub> =250µA	30	-	-	V
I <sub>DSS</sub>	Zero Gate Voltage Drain Current	V <sub>DS</sub> =30V, V <sub>GS</sub> =0V,	-	-	1.0	μΑ
I <sub>GSS</sub>	Gate to Body Leakage Current	V <sub>DS</sub> =0V, V <sub>GS</sub> = ±20V	-	-	±100	nA
V <sub>GS(th)</sub>	Gate Threshold Voltage	V <sub>DS</sub> =V <sub>GS</sub> , I <sub>D</sub> =250μA	1.0	1.5	2.5	V
D	Static Drain-Source on-Resistance	V <sub>GS</sub> =10V, I <sub>D</sub> =4A	-	29	38	
$R_{DS(on)}$		V <sub>GS</sub> =4.5V, I <sub>D</sub> =3A	-	45	65	mΩ
C <sub>iss</sub>	Input Capacitance	\/ -45\/ \/ -0\/	-	233	-	pF
Coss	Output Capacitance	<ul><li>V<sub>DS</sub>=15V, V<sub>GS</sub>=0V,</li><li>f=1.0MHz</li></ul>	-	44	-	pF
C <sub>rss</sub>	Reverse Transfer Capacitance	I-1.UIVIDZ	-	33	-	pF
Qg	Total Gate Charge	\/ -45\/   -04	-	3	-	nC
Q <sub>gs</sub>	Gate-Source Charge	$V_{DS}$ =15V, $I_{D}$ =2A,	-	0.5	-	nC
Q <sub>gd</sub>	Gate-Drain("Miller") Charge	V <sub>GS</sub> =10V	-	0.8	-	nC
t <sub>d(on)</sub>	Turn-on Delay Time	1/ 451/	-	4	-	ns
t <sub>r</sub>	Turn-on Rise Time	V <sub>DS</sub> =15V,	-	2.1	-	ns
t <sub>d(off)</sub>	Turn-off Delay Time	$I_D=4A$ , $R_{GEN}=3\Omega$ ,	-	15	-	ns
t <sub>f</sub>	Turn-off Fall Time	V <sub>GS</sub> =10V	-	3.2	-	ns
	Maximum Continuous Drain to Source Diode Forward Current				4.5	
Is			-	-	4.5	Α
I <sub>SM</sub>	Maximum Pulsed Drain to Source Diode Forward Current		-	-	16	Α
	Drain to Source Diode Forward	in to Source Diode Forward			1.2	V
$V_{SD}$	Voltage	$V_{GS}=0V$ , $I_{S}=4A$	-	_	1.2	\ \ \

Notes:1. Repetitive Rating: Pulse Width Limited by Maximum Junction Temperature

<sup>2.</sup> Pulse Test: Pulse Width≤300µs, Duty Cycle≤0.5%



# **Typical Performance Characteristics**

Figure1: Output Characteristics

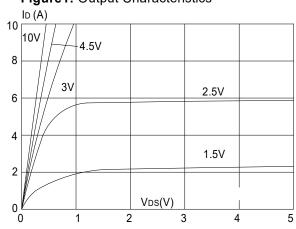


Figure 2: Typical Transfer Characteristics

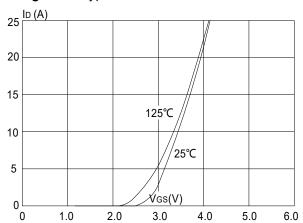


Figure 3:On-resistance vs. Drain Current

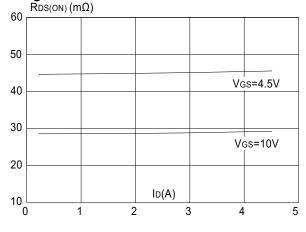


Figure 4: Body Diode Characteristics

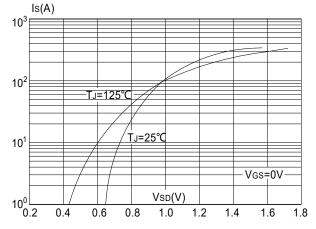


Figure 5: Gate Charge Characteristics

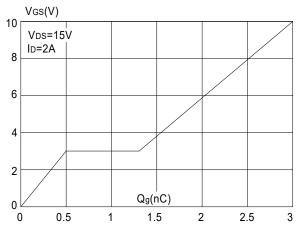
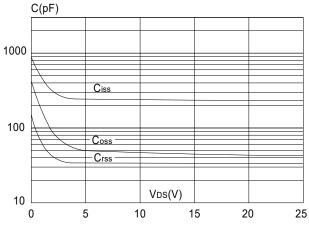
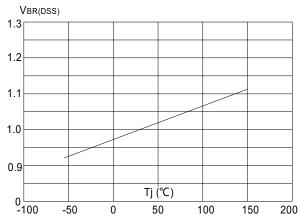


Figure 6: Capacitance Characteristics





**Figure 7:** Normalized Breakdown Voltage vs. Junction Temperature



**Figure 8:** Normalized on Resistance vs. Junction Temperature

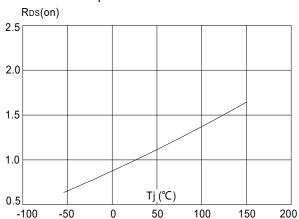
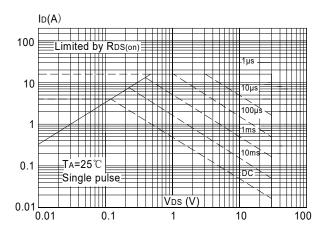
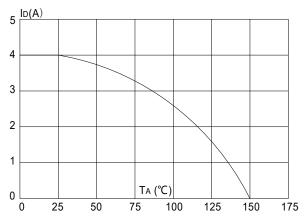


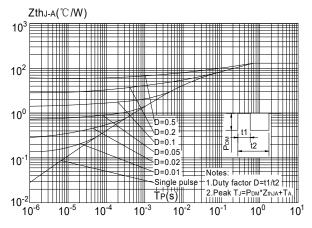
Figure 9: Maximum Safe Operating Area



**Figure 10:** Maximum Continuous Drain Current vs. Ambient Temperature

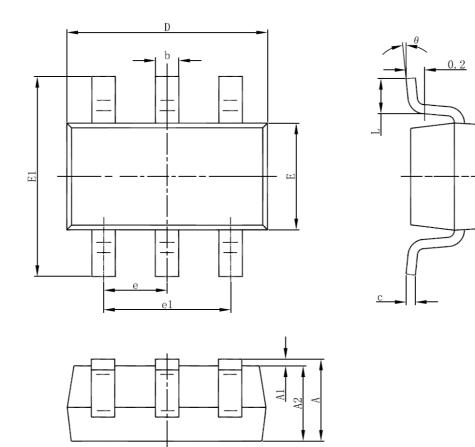


**Figure.11:** Maximum Effective Transient Thermal Impedance, Junction-to-Ambient





## **SOT-23-6L Package Information**



Symbol	Dimensions In Millimeters		Dimensions In Inches		
	Min	Max	Min	Max	
Α	1.050	1.250	0.041	0.049	
A1	0.000	0.100	0.000	0.004	
A2	1.050	1.150	0.041	0.045	
b	0.300	0.500	0.012	0.020	
С	0.100	0.200	0.004	0.008	
D	2.820	3.020	0.111	0.119	
E	1.500	1.700	0.059	0.067	
E1	2.650	2.950	0.104	0.116	
е	0.950(BSC)		0.037(BSC)		
e1	1.800	2.000	0.071	0.079	
L	0.300	0.600	0.012	0.024	
θ	0°	8°	0°	8°	



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